

Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga; Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.
Physica B : condensed matter 2009 / 23/24, p. 5153-5155 : ill

Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga; Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.
Radiation Interaction with Materials and its use in Technologies : Kaunas, 24-27.09.2008 2008 / p. 204-207